

Fig.1

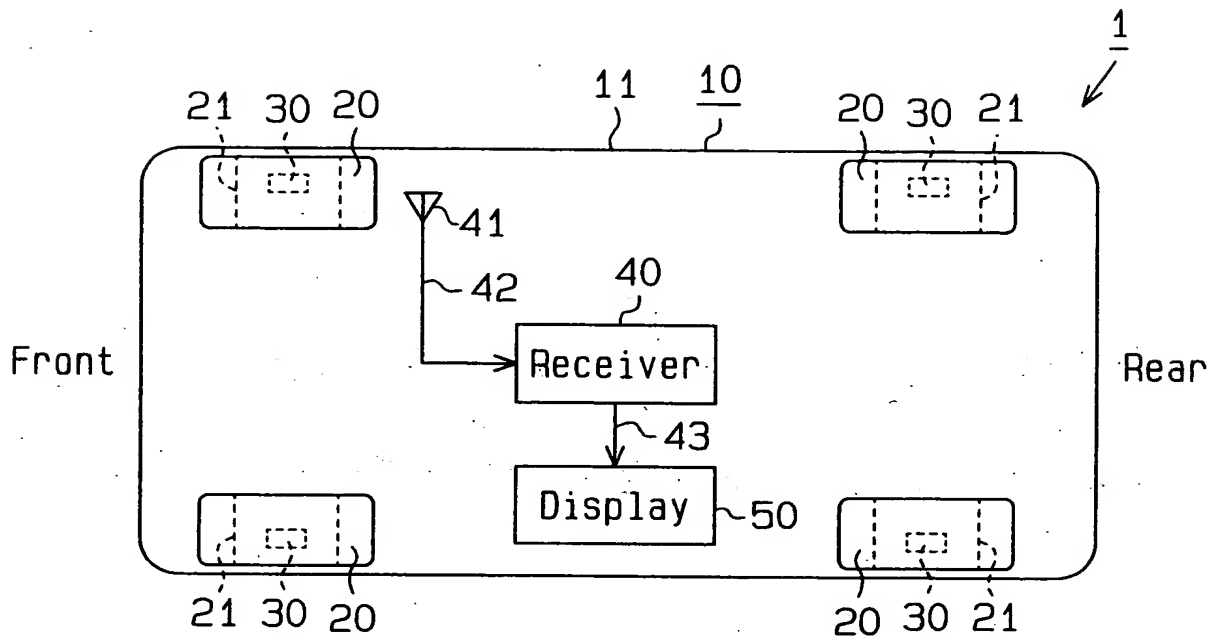


Fig.2

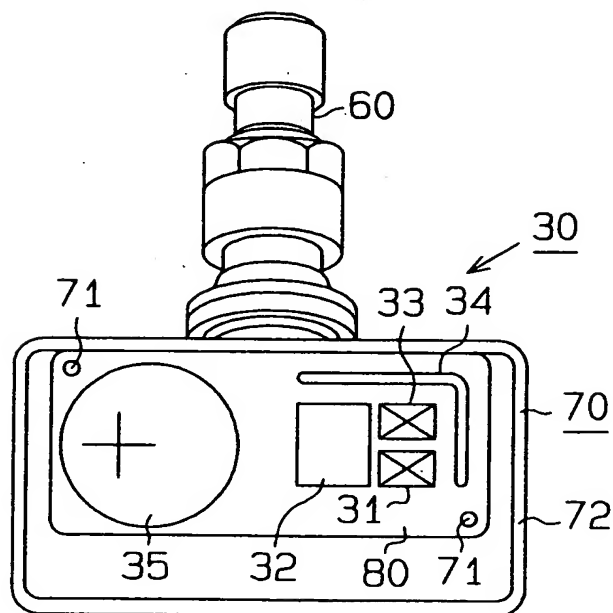
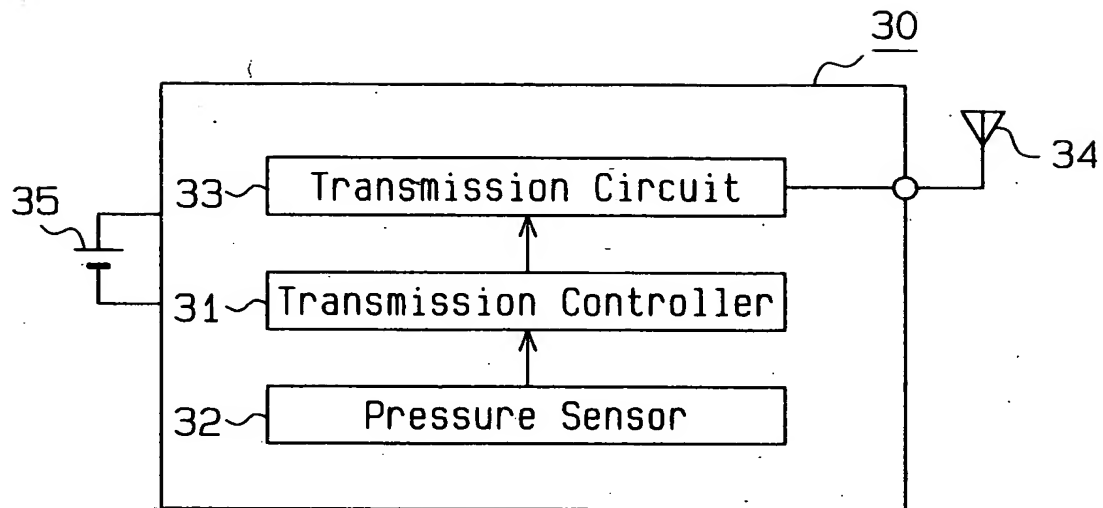
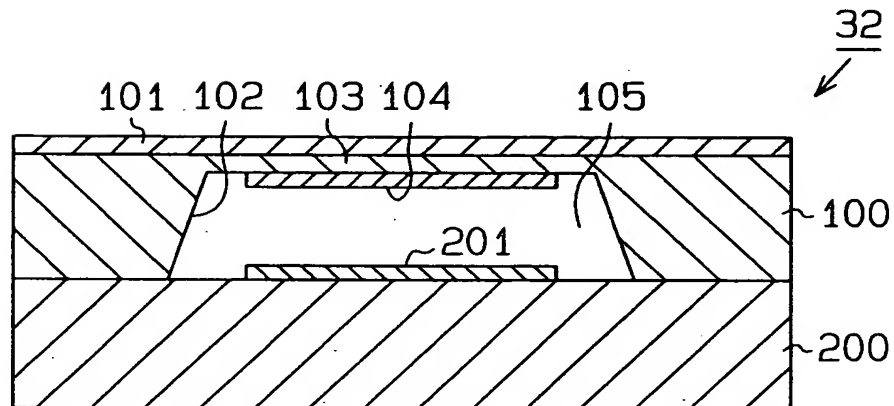


Fig.3**Fig.4**

A cross-sectional view of a semiconductor device 32. The device consists of a substrate 80 with a layer 35 on top. A gap 300 is formed in the layer 35. On the right side of the gap, there is a structure 100. This structure 100 includes a layer 101 on top of a layer 103, which is on top of a layer 200. The layer 200 is on top of the substrate 80. An arrow points to the device 32.

[illegible]